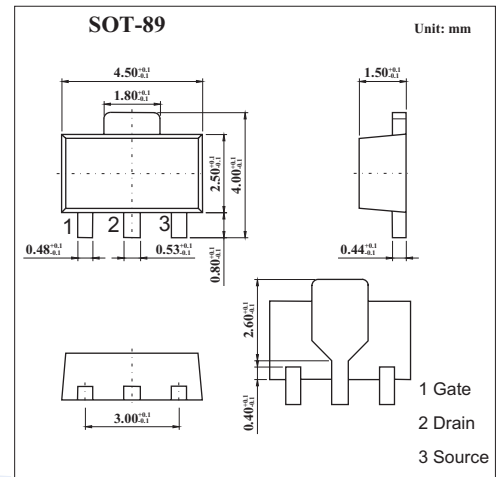


P-Channel MOS Silicon FET

2SJ288

■ Features

- Low on resistance
- Very high-speed switching
- Low-voltage drive



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage V _{GS} =0	V _{DSS}	-60	V
Gate to source voltage V _{DS} =0	V _{GSS}	± 15	V
Drain current (DC)	I _D	-500	m A
Drain current(pulse) *	I _D	-2	A
Power dissipation	P _D	3.5	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10 μs; d ≤ 1%.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	I _{DSS}	V _{DS} =-60V, V _{GS} =0			-100	μ A
Gate leakage current	I _{GSS}	V _{GS} =± 12V, V _{DS} =0			± 10	μ A
Gate cut-off voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-1.0		-2.0	V
Forward transfer admittance	Y _{fs}	V _{DS} =-10V, I _D =-250mA	240	400		ms
Drain to source on-state resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-250mA		2.2	3.0	Ω
		V _{GS} =-4V, I _D =-250mA		3.0	4.0	Ω
Input capacitance	C _{iss}	V _{DS} =-20V, V _{GS} =0, f=1MHZ		45		pF
Output capacitance	C _{oss}			20		pF
Reverse transfer capacitance	C _{rss}			5		pF
Turn-on delay time	t _{d(on)}				7	
Rise time	t _r	V _{DD} =-30V, I _D =-250mA R _L =120 Ω		10		ns
Turn-off delay time	t _{d(off)}			35		ns
Fall time	t _f				20	

■ Marking

Marking	JE
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